

# Nanoimprinted Perovskite Micro- Nanostructures for Photovoltaics

Bala Balachandran<sup>1</sup>, Ross Haroldson<sup>1</sup>, Yixin Ren, Honglei Wang, Julia Y. Chan, Anvar Zakhidov\*,  
Walter Hu\*

<sup>1</sup>*Equal contribution. The University of Texas at Dallas, Richardson, TX 75080*

\*Corresponding Authors: [walter.hu@utdallas.edu](mailto:walter.hu@utdallas.edu), [zakhidov@utdallas.edu](mailto:zakhidov@utdallas.edu)

Perovskites (PS) have quickly emerged as a promising material for photovoltaics (PV) with 21% power conversion efficiency (PCE) in the shortest time in history of solar cells. To our best knowledge, there is no report yet on the use of nanoimprint lithography (NIL) on organic-inorganic perovskites MAPbBr<sub>(3-x)</sub>I<sub>x</sub>. It is not surprising that since MAPbI<sub>3</sub> is crystalline material without glass transition, it is expected to be not imprintable. On the other hand it is obvious that nanopatterning of perovskites, if it would be achieved, has a great potential to tune and improve the electronic properties via larger surface for charge collection, higher mobility, and longer life times, similar to nanoimprinted organic PV, and optical processes via better light absorption, comparable to the successes of NIL patterning for silicon PV.

Towards this end, here we report the use of nanoimprint to pattern perovskites into ordered micro and nanostructures with improved crystallinity and light absorption. Although PS are ionic solids and do not have a glass-transition behavior like polymer, it becomes “soft” enough to deform to fill in mold cavities upon applied heat and pressure (Fig. 1A), in particular with assistance from a underneath polymer hole transport layer in a “cushion” effect. SEM shows the successful NIL of MAPbI<sub>3</sub> films into nanogratings of well-defined crystalline groves and holes with no visible grain boundaries (Fig. 1C-1F). A simple hypothesis is that mechanism of deforming PS films during NIL is due to grain sliding/merging during the pressure driven squeezing flow of PS under elevated temperature into the mold cavities and fill film porosity, as shown at Fig. 1B. The initial porosity of the PS films plays a positive role, since they allow movement of PS grains under pressure (P~6 MPa) and temperature (T~100 °C). A microscopic mechanism of grains collision with formation of bigger grains, with better crystalline type can be understood in terms of sliding of small grains relative to each other and moving into openings of the mold, activated by high T and squeezing flow driven by high P. During the grain collision process, pinholes and boundaries that are associated with initial smaller grains are greatly reduced or even completely removed (Fig. 1D). Some of the broken gratings in the defect area show formation of single crystal PS sub-micron nanowires (Fig. 1E). Such freestanding or surface patterned perovskite nanowires may open up new opportunities to microlasing, nanoscale LED, photodetectors. The NIL patterns in PS (Fig 1G) also show the photonic crystal color effects, such as bright iridescence, suggesting that with proper structural design, favorable photon trapping for higher optical absorption is feasible.

We then use X-ray diffraction (XRD) to investigate crystallinity of the nanoimprinted MAPbI<sub>3</sub>. The crystallite size before NIL and after NIL were determined using Rietveld refinement based on all *hkl* reflections to be 68.3 nm and 187.9 nm, respectively. The (220) reflection of before and after NIL are shown in Fig 2B. The narrower reflection in the red curve indicates the significantly increased crystallinity. For proof-of-concept, we are just able to make prototype devices using the successfully imprinted MAPbI<sub>3</sub> films as shown in Fig. 1C on a PEDOT:PSS covered ITO glass. Fig. 3 shows the J-V curves of NIL- MAPbI<sub>3</sub> PSPV vs. flat PSPV. Clearly in first trials, the nanoimprinted PSPV shows dramatic effect of photocurrent enhancement likely due to significantly improved crystallinity. Low fill factor (FF) and low open circuit voltage  $V_{oc} \sim 0.34$  V are likely due to imprint defect areas of 1 cm<sup>2</sup> pixels, which will be mitigated in future work.

